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Substitute for form 1449PTO			Complete if Known		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Application Number		
			Filing Date		
			First Named Inventor	Oleg GRUDIN et al.	
			Art Unit		
			Examiner Name		
Sheet	1	of	2	Attorney Docket Number	14836-8US-2 AD/mb

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
COH		US-4,472,239	18 Sep. 1984	Robert E. Higashi et al.	
		US-5,635,893	3 June 1997	Renwin J. Yee et al.	
		US-5,466,484	14 Nov. 1995	Gary L. Spraggins et al.	
		US-5,679,275	21 Oct. 1997	David M. Susak et al.	
		US-4,870,472	26 Sep. 1989	Robert L. Vyne	
		US-6,184,494	6 Feb. 2001	Arto Isokoski et al.	
		US-5,742,307	21 Apr. 1998	William G. Hawkins	
		US-4,210,996	Jul. 8, 1980	Yoshihito Amemiya et al.	
		US-4,782,202	Nov. 1, 1988	Takafumi Endo et al.	
		US-2002/033519	Mar. 21, 2002	Jeffrey A. Babcock et al.	
COH		US-6,255,185	Jul. 3, 2001	Douglas D. Coolbaugh et al.	
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FOREIGN PATENT DOCUMENTS						
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		Country Code ³ - Number ⁴ - Kind Code ⁵ (if known)				
COH		WO03/023794	Mar. 20, 2003	Oleg Grudin et al.		
		EP 1 275 967	Jan. 15, 2003	Honeywell Inc.		

Examiner Signature	TU HOANG	Date Considered	1/19/06
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NON PATENT LITERATURE DOCUMENTS			
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		Pulse Current Trimming of Polysilicon Resistors, D.W. Feldbaumer et al., IEEE Transactions on Electron Devices, IEEE, N.Y., USA, Vol. 42, N° 4, pp. 689-696.	
		Dopant Segregation in Polycrystalline Silicon, Mandurah et al., Journal Appl. Phys. 51(11), November 1980, pp. 5755-5763.	
		Spin-on Nanoparticle Tin Oxide for Microhotplate Gas Sensors, R. E. Cavicchi et al. Sensor and Actuators B. Elsevier Sequoia, S.A. Lausanne, CH, Vol. 77, No. 1-2, June 15, 2001, pp. 145-154.	
		A characterization of the Thermal Parameters of Thermally Driven Polysilicon Microbridge Actuators Using Electrical Impedance Analysis, Jae-Youl Lee et al., Sensors and Actuators A, Elsevier Sequoia S.A., Lausanne, CH. Vol. 75, No. 1, May 4, 1999, pp. 86-92.	
		Fabrication of Thermal-Isolation Structure for Microheater Elements Applicable to Fingerprint Sensors, Hans Ji-Song et al., Sensors and Actuators A, Elsevier Sequoia S.A., Lausanne, CH, Vol. 100, No. 1, Aug. 15, 2002, pp. 114-122.	

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Substitute for form 1449PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet	1	of	3
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Complete if Known

Application Number	10/796,420
Filing Date	March 10, 2004
First Named Inventor	Oleg GRUDIN et al.
Art Unit	3742
Examiner Name	(unknown)
Attorney Docket Number	14836-8US-2 AD/mb

#U.S. PATENT DOCUMENTS

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FOREIGN PATENT DOCUMENTS

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		Filing Date	March 10, 2004
		First Named Inventor	Oleg GRUDIN et al.
		Art Unit	3742
		Examiner Name	(unknown)
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		Constant Voltage Trimming of Heavily Doped Polysilicon Resistors, Japan Journal Appl. Phys. Vol. 34, Part 1, No. 1, January 1995, pp. 48-53.	
		Pulse Current Trimming of Polysilicon Resistors, Transactions of Electron Devices, IEEE, Vol. 42, N° 4, April 1995, pp. 689-695.	
		Change in Temperature Coefficient of Resistance of Heavily Doped Polysilicon Resistors Caused by Electrical Trimming, Japan Journal Appl. Phys. Vol. 35, Part 1, No. 8, August 1995, pp. 4209-4215.	
		Theory and Application of Polysilicon Resistor Trimming, Solid-State Electronics, Vol. 38, N° 11, 1995, pp. 1861-1869.	
		Electrical Trimming of Ion-Beam Sputtered Polysilicon Resistors by High Current Pulses, IEEE Transactions on Electron Devices, Vol. 41, No. 8, August 1994, pp. 1429-1434.	
		Electrical Trimming of Heavily Doped Polycrystalline Silicon Resistors, IEEE Transactions on Electron Devices, Vol. ED-26, No. 11, November 1979, pp. 738-742.	
		A Monolithic 14Bit D/A Converter Fabricated with a New Trimming Technique (DOT), IEEE, Journal of Solid-State Circuits, Vol. SC-19, N° 5, October 1984, pp. 802-807.	
		Precision Electrical Trimming of Very Low TCR Poly-SiGe Resistors, IEEE Electron Device Letters, Vol. 21, No. 6, June 2000, pp. 283-286.	
		1/f Noise Transformation that Accompanies the Trimming of Polycrystalline Silicon Layers, Solid State Phenomena, Vols. 51-52 (1996) Scitec Publications, Switzerland, pp. 391-396.	
		Micromachined Thermal Radiation Emitter from a Commercial CMOS Process, IEEE Electron Devices Letters, Vol. 12, No. 2, February 1991, pp. 57-59.	

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NON PATENT LITERATURE DOCUMENTS			
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		CMOS-Compatible High-Temperature Micro-Heater: Microstructure Release and Testing, Can. J. Elect & Comp. Eng., Vol. 25, No. 1, January 2000, pp. 002-006.	
		Reliability Study of Polysilicon for Microhotplates, 1994, Dept. of Electrical and Computer Engineering, N.R. Swart et al., University of Waterloo, Waterloo, Ont. CANADA, pp. 119-122,	
		CMOS Thermally Isolated Heater Structure as a Substrate for Semiconductor Gas Sensors, S. Wessel et al, Energy Research Institute, pp. 1.6.1 to 1.6.8.	
		A Microstructure for Measurement of Thermal Conductivity of Polysilicon Thin Films, Friedemann Völklein et al., Jour. of Microelectromechanical Systems, Vol. 1, N° 4, Dec. 1992, pp. 193-196.	
		Electrical and Optical Characteristics of Vacuum-Sealed Polysilicon Microlamps, Carlos H. Mastrangelo et al., IEEE Transactions on Electron Devices, Vol. 39, N° 6, June 1992, pp. 1363-1374.	

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